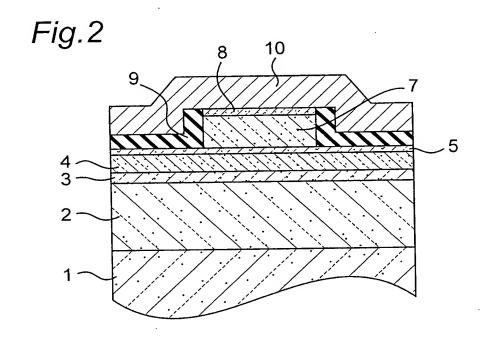
Title: SEMICONDUCTOR LASER DEVICE Inventors: NISHIGUCHI et al. Atty Docket No.: 402859 Leydig, Voit & Mayer 202-737-6770

Fig. 1

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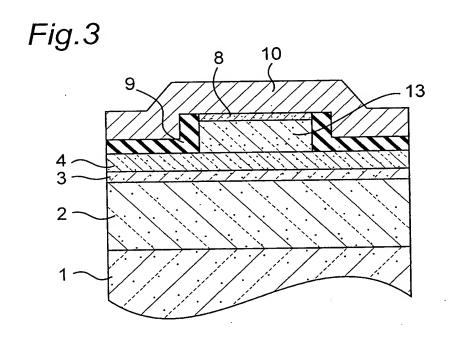


Fig.4

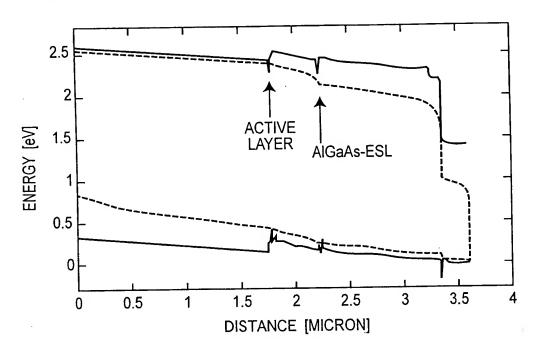
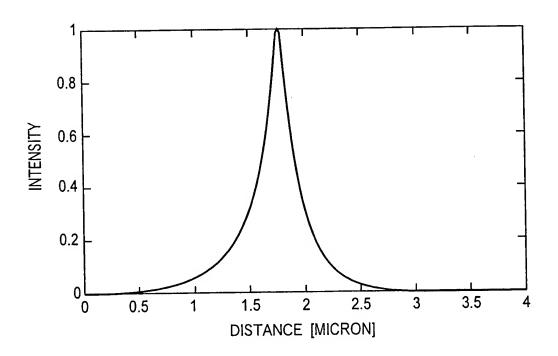


Fig.5



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Fig.6 2 ACTIVE | LAYER AlGaInP/GaInP-ESL ENERGY [eV] 1.5 0.5 0 3.5 1.5 2.5 3 0.5

DISTANCE [MICRON]

0

1

Fig.7 AlGainP/GainP-ESL 0.8 0.6 INTENSITY 0.4 0.2 0 0 L 3.5 2.5 3 1.5 0.5 DISTANCE [MICRON]

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Fig.8

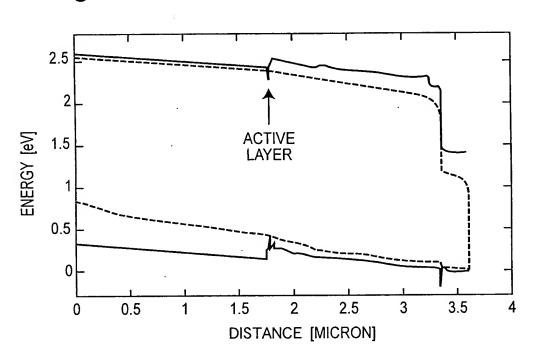
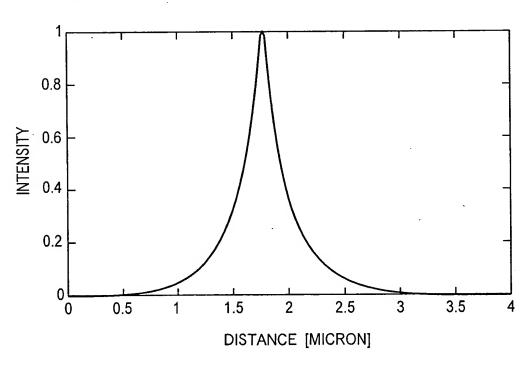


Fig.9



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Fig. 10

